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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

pplicant: Charl

Charles H. Dennison

§ Group Art Unit:

2811

Serial No.:

10/633,886

§ §

Examiner:

Steven Loke

Filed:

For:

August 4, 2003

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Damascene Conductive Line

Atty. Dkt. No.:

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(P15589)

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Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant submits the references listed on the attached form PTO 1449, copies of which are enclosed. A copy of a communication dated December 14, 2004 from a foreign patent office in a counterpart application is also enclosed. I, the undersigned, hereby certify that each item of information contained in the Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement. Please apply any charges or credits to Deposit Account No. 20-1504 (ITO.0544US).

Respectfully submitted,

January 18, 2005

Date

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Date of Deposit: January 18, 2005

I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as **first class mail** with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, P.O. Box 1450,

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Alexandria, VA 22313-1450.

Monica Jacobs

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					APPL:CANT(S):		10/000,000		
		lse several sheets if ne			CHARLES H. DENNI				
JAN 2 ° 2015					August 4, 2003		GROUP ART UNIT: 2811		
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS	IF APPRO	OPRIATE
	Α.	5,970,336	10/19/1999	Wolsten	Wolstenholme et al.				
	B.	6,567,293	05/20/2003	Lowrey	Lowrey et al.				
	C.								
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	E.								
	F.								
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	Н.								
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	I.	DD 251 225 A1	11/04/1987	Dutch					
	J.	WO 2004/090984	10/21/2004	PCT					
	K.								
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	P.	Horii, H., Yi, J.H., Park, J.H., Ha, Y.H., Baek, I.G., Park, S.O., Hwang, Y.N., Lee, S.H., Kim, Y.T., Lee, K.H., Chung, U-In and Moon, J.T., "A Novel Cell Technology Using N-doped GeSbTe Films for Phase Change RAM," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003							
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

PTO-1449

Page 1 of 1

DATE CONSIDERED

**EXAMINER**